Darlington Complementary Silicon Power Transistors

TIP140, TIP141, TIP142, (NPN); TIP145, TIP146, TIP147, (PNP)

Designed for general-purpose amplifier and low frequency switching applications.



• High DC Current Gain -

Min
$$h_{FE} = 1000 @ I_C$$

= 5.0 A, $V_{CE} = 4 V$

• Collector-Emitter Sustaining Voltage - @ 30 mA

- Monolithic Construction with Built-In Base-Emitter Shunt Resistor
- These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	TIP140 TIP145	TIP141 TIP146	TIP142 TIP147	Unit
Collector - Emitter Voltage	V_{CEO}	60	80	100	Vdc
Collector - Base Voltage	V _{CB}	60	80	100	Vdc
Emitter - Base Voltage	V _{EB}		5.0		Vdc
Collector Current - Continuous - Peak (Note 1)	I _C	10 15		Adc	
Base Current - Continuous	Ι _Β		0.5		Adc
Total Power Dissipation @ T _C = 25°C	P _D		125		W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	_	65 to +15	0	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	35.7	°C/W

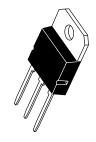
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



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10 AMPERE
DARLINGTON
COMPLEMENTARY SILICON
POWER TRANSISTORS
60-100 VOLTS, 125 WATTS



SOT-93 (TO-218) CASE 340D STYLE 1



TO-247 CASE 340L STYLE 3

NOTE: Effective June 2012 this device will be available only in the TO-247 package. Reference FPCN# 16827.

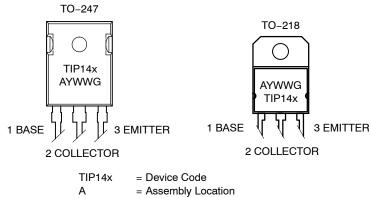
ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{1. 5} ms, ≤ 10% Duty Cycle.

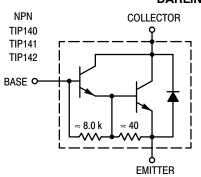
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

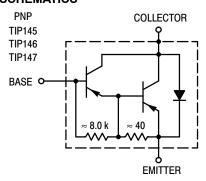
MARKING DIAGRAMS



TIP14x = Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

DARLINGTON SCHEMATICS





ORDERING INFORMATION

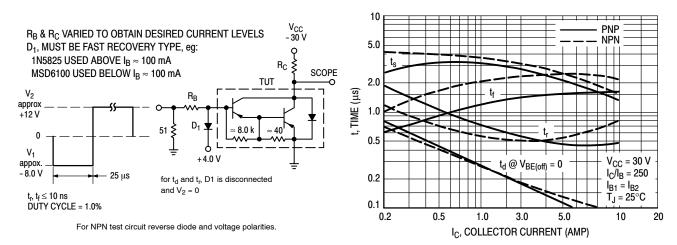
Device	Package	Shipping
TIP140G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP141G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP142G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP145G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP146G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP147G	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP140G	TO-247 (Pb-Free)	30 Units / Rail
TIP141G	TO-247 (Pb-Free)	30 Units / Rail
TIP142G	TO-247 (Pb-Free)	30 Units / Rail
TIP145G	TO-247 (Pb-Free)	30 Units / Rail
TIP146G	TO-247 (Pb-Free)	30 Units / Rail
TIP147G	TO-247 (Pb-Free)	30 Units / Rail

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS	<u>.</u>		•			•
Collector-Emitter Sustaining Voltage (Note 2)		V _{CEO(sus)}				Vdc
$(I_C = 30 \text{ mA}, I_B = 0)$	TIP140, TIP145	020(040)	60	_	_	
	TIP141, TIP146		80	_	_	
	TIP142, TIP147		100	-	-	
Collector Cutoff Current		I _{CEO}				mA
$(V_{CE} = 30 \text{ Vdc}, I_{B} = 0)$	TIP140, TIP145	020	_	_	2.0	
$(V_{CE} = 40 \text{ Vdc}, I_{B} = 0)$	TIP141, TIP146		_	_	2.0	
$(V_{CE} = 50 \text{ Vdc}, I_B = 0)$	TIP142, TIP147		-	-	2.0	
Collector Cutoff Current		I _{CBO}				mA
$(V_{CB} = 60 \text{ V}, I_{E} = 0)$	TIP140, TIP145	020	_	_	1.0	
$(V_{CB} = 80 \text{ V}, I_{E} = 0)$	TIP141, TIP146		_	_	1.0	
$(V_{CB} = 100 \text{ V}, I_E = 0)$	TIP142, TIP147		-	_	1.0	
Emitter Cutoff Current (V _{BE} = 5.0 V)		I _{EBO}	_	_	2.0	mA
ON CHARACTERISTICS (Note 2)						
DC Current Gain		h _{FE}				_
$(I_C = 5.0 \text{ A}, V_{CE} = 4.0 \text{ V})$			1000	-	_	
$(I_C = 10 \text{ A}, V_{CE} = 4.0 \text{ V})$			500	-	-	
Collector-Emitter Saturation Voltage		V _{CE(sat)}				Vdc
$(I_C = 5.0 \text{ A}, I_B = 10 \text{ mA})$			_	-	2.0	
$(I_C = 10 \text{ A}, I_B = 40 \text{ mA})$			-	-	3.0	
Base-Emitter Saturation Voltage		V _{BE(sat)}	-	_	3.5	Vdc
$(I_C = 10 \text{ A}, I_B = 40 \text{ mA})$, ,				
Base-Emitter On Voltage		V _{BE(on)}	-	_	3.0	Vdc
$(I_C = 10 \text{ A}, V_{CE} = 4.0 \text{ Vdc})$. ,				
SWITCHING CHARACTERISTICS						
Resistive Load (See Figure 1)						
Delay Time		t _d	-	0.15	-	μS
•						
Rise Time $(V_{CC} = 30 \text{ V}, I_C = 5.0 \text{ A}, I_B = 20 \text{ mA}, \text{ Duty Cycle} \le 2.0$		t _r	_	0.55	_	μs

^{2.} Pulse Test: Pulse Width = 300 $\mu s,$ Duty Cycle \leq 2.0%.

Fall Time



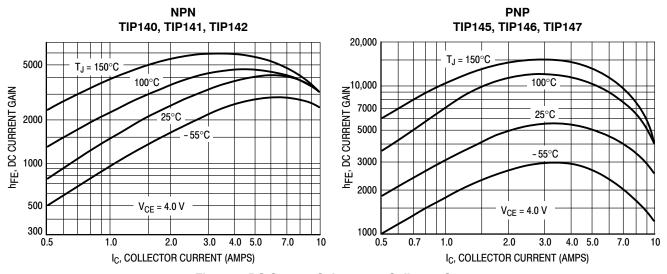
 t_{f}

Figure 1. Switching Times Test Circuit

Figure 2. Switching Times

2.5

TYPICAL CHARACTERISTICS



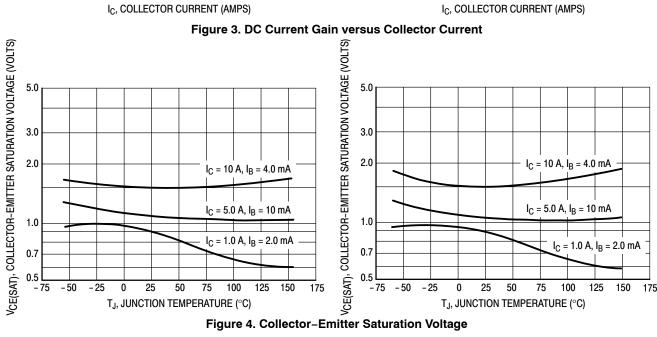


Figure 4. Collector-Emitter Saturation Voltage

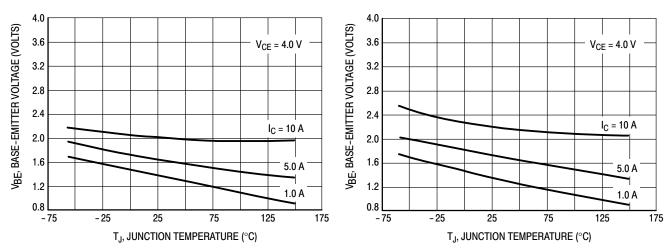


Figure 5. Base-Emitter Voltage

ACTIVE-REGION SAFE OPERATING AREA

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

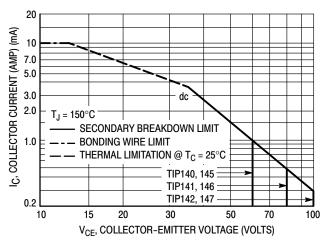


Figure 6. Active-Region Safe Operating Area

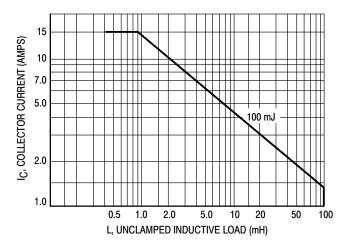
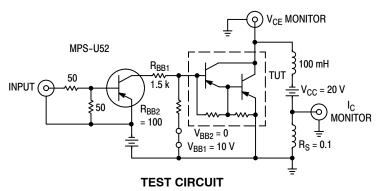
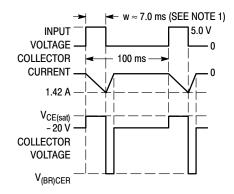


Figure 7. Unclamped Inductive Load



NOTE 1: Input pulse width is increased until I_{CM} = 1.42 A.

NOTE 2: For NPN test circuit reverse polarities.



VOLTAGE AND CURRENT WAVEFORMS

Figure 8. Inductive Load

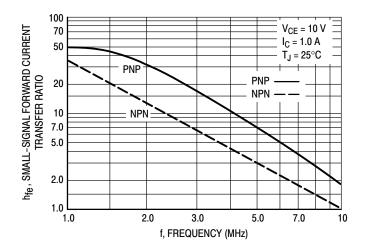


Figure 9. Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio

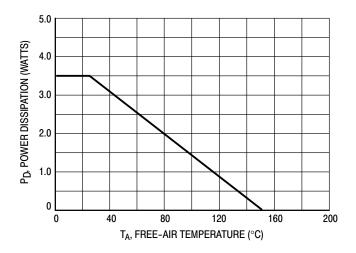
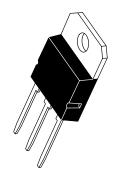


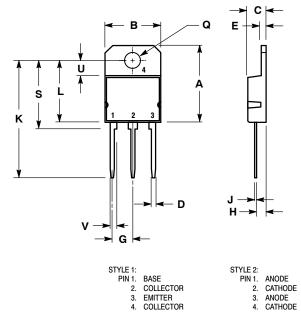
Figure 10. Free-Air Temperature Power Derating



SOT-93 (TO-218) CASE 340D-02 **ISSUE E**

DATE 01/03/2002

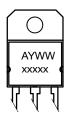




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.

			INCHES		
	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α		20.35		0.801	
В	14.70	15.20	0.579	0.598	
С	4.70	4.90	0.185	0.193	
D	1.10	1.30	0.043	0.051	
Е	1.17	1.37	0.046	0.054	
G	5.40	5.55	0.213	0.219	
Н	2.00	3.00	0.079	0.118	
7	0.50	0.78	0.020	0.031	
K	31.00	REF	1.220 REF		
L		16.20		0.638	
Q	4.00	4.10	0.158	0.161	
S	17.80	18.20	0.701	0.717	
U	4.00 REF		0.157 REF		
V	1 75 RFF		0.0	169	

MARKING DIAGRAM



= Assembly Location

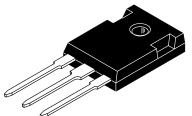
= Year

WW = Work Week XXXXX = Device Code

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TO-247 CASE 340L ISSUE G

DATE 06 OCT 2021

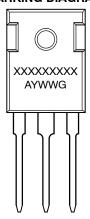
NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER

	MILLIMETERS		INC	HES	
DIM	MIN.	MAX.	MIN.	MAX.	
Α	20.32	21.08	0.800	0.830	
В	15.75	16.26	0.620	0.640	
С	4.70	5.30	0.185	0.209	
D	1.00	1.40	0.040	0.055	
Ε	1.90	2.60	0.075	0.102	
F	1.65	2.13	0.065	0.084	
G	5.45	5.45 BSC		0.215 BSC	
Н	1.50	2.49	0.059	0.098	
J	0.40	0.80	0.016	0.031	
К	19.81	20.83	0.780	0.820	
L	5.40	6.20	0.212	0.244	
N	4.32	5.49	0.170	0.216	
Р		4.50		0.177	
Q	3.55	3.65	0.140	0.144	
U	6.15	6.15 BSC 0.242 I		BSC	
W	2.87	3.12	0.113	0.123	

⊕ 0.25 (0.010)**W** Y AS

GENERIC MARKING DIAGRAM*



STYLE 1:	STYLE 2:	STYLE 3: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 4:
PIN 1. GATE	PIN 1. ANODE		PIN 1. GATE
2. DRAIN	2. CATHODE (S)		2. COLLECTOR
3. SOURCE	3. ANODE 2		3. EMITTER
4. DRAIN	4. CATHODES (S)		4. COLLECTOR

PIN 1. MAIN TERMINAL 1 2. MAIN TERMINAL 2

3. GATE 4. MAIN TERMINAL 2 XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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STYLE 5: PIN 1. CATHODE

2. ANODE

3. GATE 4. ANODE

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NTE247 NTE248 NTE248 NTE253 NTE2548 NTE261